Thyristor Semiconductor Device - Page 1 of 1



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Inclosure Materia	al:
Metal	
Overall Length:	
Between 0.240 in	ches and 0.260 inches
Overall Diameter	r:
Between 0.335 in	ches and 0.370 inches
Mounting Metho	d:
Terminal	
Features Provide	ed:
Hermetically seale	ed case
Semiconductor I	Material:
Silicon	
Voltage Rating I	n Volts Per Characteristic:
500.0 repetitive p	beak off-state voltage
Current Rating P	Per Characteristic:
2.50 amperes for	ward current, total rms nanoamperes and 100.00 amperes peak forward surge current nanoamperes
Power Rating Pe	er Characteristic:
16.0 watts small-s	signal input power, common-collector blank
Maximum Opera	ting Tempurature Per Measurement Point:
110.0 degrees ce	Isius ambient air
Special Features	S:
Third terminal ma	y be omitted
Test Data Docun	nent:
70210-944147 dra	awing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.
excludes any spe	cification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type A	nd Quantity:
3 uninsulated wire	e lead
Shelf Life:	
N/a	
Unit Of Measure	:
Demilitarization:	
No	
Fiig:	
A110a0	